



DOCKET NO: 246155US2SRD

IN THE UNITED STATES PATENT & TRADEMARK OFFICE

IN RE APPLICATION OF

:

MASATO KOYAMA, ET AL.

: EXAMINER: SHOUXIANG HU

SERIAL NO: 10/726,705

:

FILED: DECEMBER 4, 2003

: GROUP ART UNIT: 2811

FOR: A METHOD OF FORMING A
SEMICONDUCTOR DEVICE HAVING
AN AMORPHOUS/CRYSTALLINE GATE
INSULATING LAYER

:

RESPONSE

COMMISSIONER FOR PATENTS
ALEXANDRIA, VIRGINIA 22313

SIR:

Further to the telephone interview with the Examiner, Applicants respectfully submit
the remarks beginning on page 2 of this response.